



**TECHNICAL SPECIFICATIONS OF
SINGLE-PHASE SILICON BRIDGE RECTIFIER**

VOLTAGE RANGE - 50 to 1000 Volts

CURRENT - 8.0 Amperes

KBU8A/RS801-KBU8M/RS807

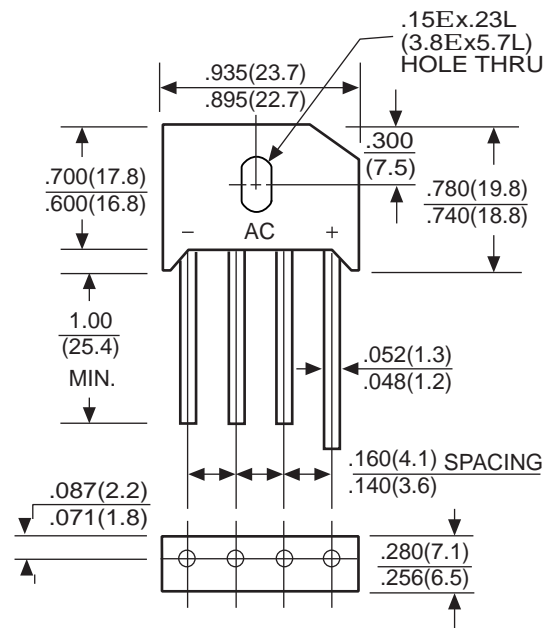
FEATURES

- * Low leakage
- * Low forward voltage
- * Surge overload rating: 250 Amperes peak

Dimensions in inches and (millimeters) KBU

MECHANICAL DATA

- * Case: Molded plastic
- * Epoxy: UL 94V-0 rate flame retardant
- * Lead: MIL-STD-202E, Method 208 guaranteed
- * Polarity: Symbols molded or marked on body
- * Mounting position: Any
- * Weight: 4.8 grams



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.
Single phase, half wave, 60 Hz, resistive or inductive load.
For capacitive load, derate current by 20%.

	SYMBOL	KBU8A	KBU8B	KBU8D	KBU8G	KBU8J	KBU8K	KBU8M	UNITS
		RS801	RS802	RS803	RS804	RS805	RS806	RS807	
Maximum Recurrent Peak Reverse Voltage	V _{RRM}	50	100	200	400	600	800	1000	Volts
Maximum RMS Bridge Input Voltage	V _{RMS}	35	70	140	280	420	560	700	Volts
Maximum DC Blocking Voltage	V _{DC}	50	100	200	400	600	800	1000	Volts
Maximum Average Forward Rectified Output Current at T _c = 75°C	I _o	8.0							Amps
Peak Forward Surge Current 8.3 ms single half sine-wave superimposed on rated load	I _{FSM}	250							Amps
Maximum Forward Voltage Drop per element at 4.0A DC	V _F	1.0							Volts
Maximum DC Reverse Current at Rated	I _R	@T _A = 25°C							uAmps
DC Blocking Voltage per element		@T _c = 100°C							
I ² t Rating for Fusing (t<8.3ms)	I ² t	127							A ² Sec
Typical Junction Capacitance (Note1)	C _J	186							pF
Typical Thermal Resistance (Note 2)	R _{θJA}	10							°C/W
Operating and Storage Temperature Range	T _J ,T _{STG}	-55 to + 150							°C

NOTES : 1. Measured at 1 MHz and applied reverse voltage of 4.0 volts
2. Thermal Resistance from Junction to Ambient and from junction to leadmounted on P.C.B. with 0.47 x 0.47" (12x12mm) copper pads.



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